RICOH

R5435x SERIES

Li-ION/POLYMER 2/3-CELL PROTECTOR Second protection IC

NO.EA-282-120409

OUTLINES

R5435x Series are CMOS-based high voltage tolerant over-charge protection ICs for Li-ion/Li-polymer secondary battery. The R5435x can detect overcharge of 2-cell to 3-cell Li-ion/Li-polymer batteries. The R5435x is consists of 3 voltage detectors, a voltage reference unit, an oscillator, a counter, a delay circuit, a logic circuit.

When the over-charge is detected, after the IC internally fixed delay time, the output of Cout becomes "H".

After detecting over-charge, when the cell voltage becomes lower than the over-charge released voltage, the over-charge state is released.

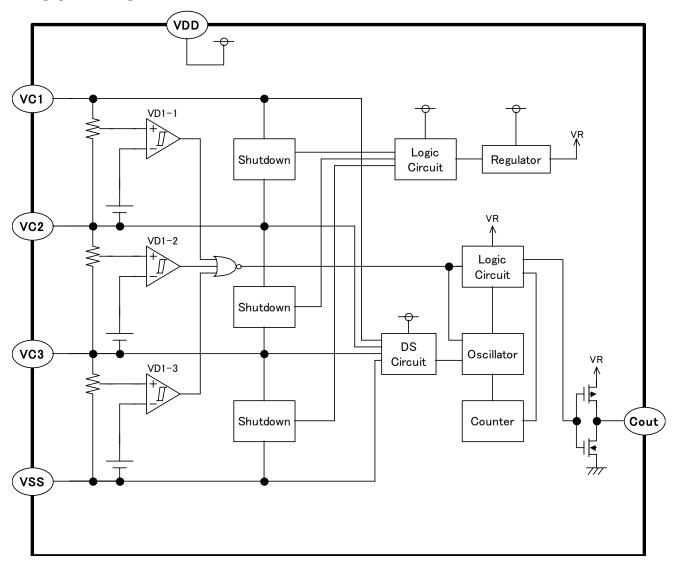
If all the cells voltages become equal or less than the shutdown detector threshold, all the circuits are halted and shut down, as a result, the consumption current of IC itself (Shutdown current) is extremely reduced.

By connect short 2 cells other than monitored cell, over-charge and released delay time can be shortened. The output type is CMOS.

FEATURES

Manufactured with High Voltage Tolerant Process Absolute Maximum Rating			30V
Low supply current	Cell voltage 3.9V, for 3	-cell	Тур. 3.0μΑ
High accuracy detector threshold	Over-charge detector	(Ta=25°C)	±20mV
		(Ta=0 to 60°C)	±25mV
Variety of detector threshold			
Over-charge detector threshold	4.1V-4.55V step of 0.00	5V (V _{DET1} n) (n=1, 2, 3)	
Over-charge released voltage	VDET1N-0V to VDET1N-0.4	/ step of 0.05V (VREL1N) (r	า=1, 2, 3)
	MIN.3.95V		
Setting of Output delay time	Over-charge detector Out	put Delay options 2, 4, 6s(B	uilt-in delay)
Shutdown Function	When all the cell volta	ges become equal or less	than shutdown
detector threshold, the IC will be into shutdown r	node and the consumption of	current of IC itself becomes	extremely small.
Even if one of the cells becomes equal or more the	nan shutdown released volta	ge, the shutdown mode is re	eleased.
Shutdown detector threshold	Typ. 3.5V±0.4V		
Shutdown Release Hysteresis	none		
Shutdown current	Max. 0.1μA		
2/3 cell protection enabler	By external wiring, 2 or	3-cell protection can be	selected.
Over-charge released condition	Released by voltage ty	ре	
Cout output	Соит: 4.7V regulator po	ower supply CMOS output	t. Active "H"
Delay Time Shortening Function	As a result of specified	setting, the delay times	are shortened,
over-charge detector time is shortened from	2sec to 1/50, 4sec and 69	sec to 1/80.	
ex. V_{C2} = V_{C3} = V_{SS} , the delay time for cell 1 is sho	ortened. Vc1=Vc2, Vc3=Vss	, the delay time for cell 2	is shortened.
$V_{C1}=V_{C2}=V_{C3}$, the delay time for cell 3 is shor	tened.		
Small package	TSOT-23-6, DFN(PLP)	1616-6B	

BLOCK DIAGRAM



SELECTION GUIDE

In the R5435Xxxxxx Series, input threshold of over-charge and output delay time can be designated according to the application.

Part Number is designated as follows:

(ex.) R5435N 301AA
$$\leftarrow$$
 Part Number $\uparrow \uparrow \uparrow \uparrow \uparrow$ a b cd

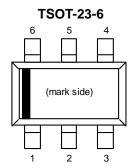
Code	Contents
а	Package Type N: TSOT-23-6, K: PLP1616-6B
b	Serial Number for the R5435 Series designating input threshold for over-charge detector
С	Designation of Output delay option
d	Designation of version symbols.

Code List

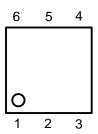
Code	V DET1 n(V) *1	V _{REL1} n(V) *1	tVDET1(s)	tVDTR1(ms)
R5435x301AA	4.450	4.150	2	16
R5435x302BA	4.350	3.950	4	16
R5435x303AA	4.350	4.050	2	16
R5435x303CA	4.350	4.050	6	6
R5435x304AA	4.400	4.100	2	16
R5435x305AA	4.300	4.000	2	16
R5435x306BA	4.450	3.950	4	16

^{*1:} n=1, 2, 3

PIN CONFIGURATIONS



DFN(PLP)1616-6B



PIN DESCRIPTION

TSOT-23-6

Pin No.	Symbol	Description
1	V_{DD}	V _{DD} Pin
2	V _{C1}	Positive terminal pin for Cell-1
3	V _{C2}	Positive terminal pin for Cell-2
4	Vсз	Positive terminal Pin for Cell-3
5	Vss	Vss pin. Ground pin for the IC
6	Соит	Output pin of over-charge detection

DFN(PLP)1616-6B

Pin No.	Symbol	Description	
1	V _{C2}	Positive terminal pin for Cell-2	
2	V _{C1}	Positive terminal pin for Cell-1	
3	V _{DD}	V _{DD} Pin	
4	Соит	utput pin of over-charge detection	
5	Vss	Vss pin. Ground pin for the IC	
6	Vсз	Positive terminal Pin for Cell-3	

^{*}The tab voltage level of the backside of the package is the substrate level (Vss).

Connect the tab to the Vss pin (Recommended) or leave the tab open.

ABSOLUTE MAXIMUM RATINGS

Ta=25°C, Vss=0V

Symbol	Item	Ratings	Unit
V_{DD}	Supply voltage	-0.3 to 30	V
V _{C1} V _{C2} V _{C3}	Input voltage Positive input pin voltage for Cell-1 Positive input pin voltage for Cell-2 Positive input pin voltage for Cell-3	Vc2 -0.3 to Vc2+6.5 Vc3 -0.3 to Vc3+6.5 -0.3 to 6.5	V
Vсоит	Output voltage Cout pin voltage	-0.3 to Vон1+0.3	V
Po	Power dissipation	460 (TSOT-23-6) 640 (PLP1616-6B)	mW
Та	Operating temperature range	-40 to 85	Ŝ
Tstg	Storage temperature range	-55 to 125	Ŝ

ELECTRICAL CHARACTERISTICS

R5435x301AA

Unless otherwise specified, Ta=25°C

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
V _{DD1}	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
V _{DET1} n	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.430	4.450	4.470	V
V DETIII	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) *Note1	4.425	4.430	4.475	V
V _{REL1} n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	4.100	4.150	4.200	V
tV _{DET1}	Output delay of over-charge	Vcelln=3.9V, Vcell1=3.9V to 4.7V (n=2,3) *Note2	1.6	2.0	2.4	S
tV _{REL1}	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsht	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tV _{DTR1}	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V tO VREL1N-0.100V tO VDET1N+0.050V to VREL1N-0.100V	8	16	24	ms
V _{OH1}	Соит Pch ON voltage1	Іон=0μA, Vcelln=4.7V (n=1,2,3)	4.0	4.7	5.4	V
V _{OH2}	Соит Pch ON voltage2	Іон=-50μA, Vcelln=4.7V (n=1,2,3)	Vон1-0.5	Vон1-0.1		V
Vol	Couт Nch ON voltage	Iol=50μA, Vcelln=3.9V (n=1,2,3)	_	0.1	0.5	V
Іѕнт	Shutdown Current	Vcelln=3.1V (n=1,2,3)	_		0.1	μA
Iss	Supply current	Vcelln=3.9V (n=1,2,3)		3.0	5.5	μΑ

^{*}Note1: This specification is guaranteed by design, not mass production tested. *Note2: VCELLn means Cell-n's voltage. n=1, 2, 3

R5435x302BA

Unless otherwise specified, Ta=25°C

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
V _{DD1}	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
V _{DET1} n	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.330	4.350	4.370	V
VDETTII	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) *Note1	4.325	4.550	4.375	V
V _{REL1} n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	3.900	3.950	4.000	V
tV _{DET1}	Output delay of over-charge	VCELLN=3.9V, VCELL1=3.9V to 4.7V (n=2,3) *Note2	3.2	4.0	4.8	s
tV _{REL1}	Output delay of release from over-charge	VCELLN=3.9V, VCELL1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsht	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tV _{DTR1}	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V tO VREL1N-0.100V tO VDET1N+0.050V to VREL1N-0.100V	8	16	24	ms
V _{OH1}	Соит Pch ON voltage1	Іон=0μA, Vcelln=4.7V (n=1,2,3)	4.0	4.7	5.4	V
V _{OH2}	Соит Pch ON voltage2	IOH=-50μA, VCELLN=4.7V (n=1,2,3)	Vон1 -0.5	Vон1 -0.1		V
Vol	Соит Nch ON voltage	Iol=50μA, Vcelln=3.9V (n=1,2,3)		0.1	0.5	V
Іѕнт	Shutdown Current	Vcelln=3.1V (n=1,2,3)			0.1	μΑ
Iss	Supply current	Vcelln=3.9V (n=1,2,3)		3.0	5.5	μΑ

^{*}Note1: This specification is guaranteed by design, not mass production tested. *Note2: VCELLn means Cell-n's voltage. $n=1,\,2,\,3$



● R5435x303AA

Unless otherwise specified, Ta=25°C

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
V _{DD1}	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
V _{DET1} n	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.330	4.350	4.370	V
V DETTII	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) *Note1	4.325	4.330	4.375	V
V _{REL1} n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	4.000	4.050	4.100	V
tV _{DET1}	Output delay of over-charge	Vcelln=3.9V, Vcell1=3.9V to 4.7V (n=2,3) *Note2	1.6	2.0	2.4	S
tV _{REL1}	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsht	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tV _{DTR1}	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V tO VREL1N-0.100V tO VDET1N+0.050V to VREL1N-0.100V	8	16	24	ms
V _{OH1}	Cout Pch ON voltage1	Іон=0μA, Vcelln=4.7V (n=1,2,3)	4.0	4.7	5.4	V
V _{OH2}	Соит Pch ON voltage2	Іон=-50μA, Vcelln=4.7V (n=1,2,3)	Vон1 -0.5	Vон1 -0.1		V
Vol	Cоuт Nch ON voltage	IoL=50μA, Vcelln=3.9V (n=1,2,3)		0.1	0.5	V
Isht	Shutdown Current	Vcelln=3.1V (n=1,2,3)			0.1	μΑ
Iss	Supply current	Vcelln=3.9V (n=1,2,3)		3.0	5.5	μA

*Note1: This specification is guaranteed by design, not mass production tested.

R5435x303CA

Unless otherwise specified, Ta=25°C

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
V _{DD1}	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
V _{DET1} n	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.330	4.350	4.370	V
VDETTII	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) *Note1	4.325	4.330	4.375	V
V _{REL1} n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	4.000	4.050	4.100	V
tV _{DET1}	Output delay of over-charge	VCELLN=3.9V, VCELL1=3.9V to 4.7V (n=2,3) *Note2	4.8	6.0	7.2	S
tV _{REL1}	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsht	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tV _{DTR1}	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V to VREL1N-0.100V to VDET1N+0.050V to VREL1N-0.100V	2	6	10	ms
V _{OH1}	Соит Pch ON voltage1	Іон=0μA, Vcelln=4.7V (n=1,2,3)	4.0	4.7	5.4	V
V _{OH2}	Соит Pch ON voltage2	IoH=-50μA, Vcelln=4.7V (n=1,2,3)	Vон1 -0.5	Vон1 -0.1		V
Vol	Couт Nch ON voltage	Iol=50μA, Vcelln=3.9V (n=1,2,3)		0.1	0.5	V
Іѕнт	Shutdown Current	Vcelln=3.1V (n=1,2,3)	_		0.1	μA
Iss	Supply current	Vcelln=3.9V (n=1,2,3)		3.0	5.5	μΑ

*Note1: This specification is guaranteed by design, not mass production tested.

*Note2: Vcelln means Cell-n's voltage. n=1, 2, 3

^{*}Note2: Vcelln means Cell-n's voltage. n=1, 2, 3

R5435x304AA

Unless otherwise specified, Ta=25°C

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
V_{DD1}	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
V _{DET1} n	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.380	4.400	4.420	V
V DETTII	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) *Note1	4.375	4.400	4.425	V
V _{REL1} n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	4.050	4.100	4.150	V
tV _{DET1}	Output delay of over-charge	Vcelln=3.9V, Vcell1=3.9V to 4.7V (n=2,3) *Note2	1.6	2.0	2.4	S
tV _{REL1}	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsht	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tV _{DTR1}	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V tO VREL1N-0.100V tO VDET1N+0.050V to VREL1N-0.100V	8	16	24	ms
V _{OH1}	Соит Pch ON voltage1	Іон=0μA, Vcelln=4.7V (n=1,2,3)	4.0	4.7	5.4	V
V _{OH2}	Couт Pch ON voltage2	Іон=-50μA, Vcelln=4.7V (n=1,2,3)	Vон1-0.5	Vон1 -0.1		V
Vol	Соит Nch ON voltage	Iol=50μA, Vcelln=3.9V (n=1,2,3)	_	0.1	0.5	V
Isht	Shutdown Current	Vcelln=3.1V (n=1,2,3)			0.1	μΑ
Iss	Supply current	Vcelln=3.9V (n=1,2,3)		3.0	5.5	μA

^{*}Note1: This specification is guaranteed by design, not mass production tested.

R5435x305AA

Unless otherwise specified, Ta=25°C

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
V _{DD1}	Operating input voltage	Voltage defined as VDD-VSS	3.3		15	V
V _{DET1} n	CELLn Over-charge threshold	Detect rising edge of supply voltage (25°C)	4.280	4.300	4.320	V
V DETIII	(n=1,2,3)	Detect rising edge of supply voltage (0 to 60°C) *Note1	4.275	4.300	4.325	V
V _{REL1} n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	3.950	4.000	4.050	V
tV _{DET1}	Output delay of over-charge	VCELLN=3.9V, VCELL1=3.9V to 4.7V (n=2,3) *Note2	1.6	2.0	2.4	S
tV _{REL1}	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsht	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tV _{DTR1}	Output delay of over-charge timer reset	VCELLn=VDET1n+0.050V to VREL1n-0.100V to VDET1n+0.050V to VREL1n-0.100V	8	16	24	ms
V _{OH1}	Соит Pch ON voltage1	Іон=0μA, Vcelln=4.7V (n=1,2,3)	4.0	4.7	5.4	V
V _{OH2}	Соит Pch ON voltage2	IOH=-50μA, VCELLN=4.7V (n=1,2,3)	Vон1 -0.5	Vон1 -0.1		V
Vol	Соит Nch ON voltage	Iol=50μA, Vcelln=3.9V (n=1,2,3)		0.1	0.5	V
Іѕнт	Shutdown Current	Vcelln=3.1V (n=1,2,3)			0.1	μA
Iss	Supply current	Vcelln=3.9V (n=1,2,3)		3.0	5.5	μΑ

^{*}Note1: This specification is guaranteed by design, not mass production tested.

^{*}Note2: VCELLn means Cell-n's voltage. n=1, 2, 3

^{*}Note2: VCELLn means Cell-n's voltage. n=1, 2, 3

R5435x306BA

Unless otherwise specified, Ta=25°C

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
V _{DD1}	Operating input voltage	Voltage defined as VDD-Vss	3.3		15	V
V _{DET1} n	CELLn Over-charge threshold (n=1,2,3)	Detect rising edge of supply voltage (25°C)	4.430	4.450	4.470	V
		Detect rising edge of supply voltage (0 to 60°C) *Note1	4.425		4.475	V
V _{REL1} n	CELLn Over-charge released voltage (n=1,2,3)	Detect falling edge of supply voltage	3.900	3.950	4.000	V
tV _{DET1}	Output delay of over-charge	Vcelln=3.9V, Vcell1=3.9V to 4.7V (n=2,3) *Note2	3.2	4.0	4.8	s
tV _{REL1}	Output delay of release from over-charge	Vcelln=3.9V, Vcell1=4.7V to 3.9V (n=2,3)	12.8	16	19.2	ms
Vsht	Shutdown detector threshold	Detect falling edge	3.1	3.5	3.9	V
tV _{DTR1}	Output delay of over-charge timer reset	VCELLN=VDET1N+0.050V to VREL1N-0.100V to VDET1N+0.050V to VREL1N-0.100V	8	16	24	ms
V _{OH1}	Соит Pch ON voltage1	Іон=0μA, Vcelln=4.7V (n=1,2,3)	4.0	4.7	5.4	V
V _{OH2}	Соит Pch ON voltage2	Іон=-50μA, Vcelln=4.7V (n=1,2,3)	Vон1 -0.5	Vон1 -0.1		V
Vol	Couт Nch ON voltage	Iol=50μA, Vcelln=3.9V (n=1,2,3)	_	0.1	0.5	V
Isht	Shutdown Current	Vcelln=3.1V (n=1,2,3)			0.1	μΑ
Iss	Supply current	Vcelln=3.9V (n=1,2,3)		3.0	5.5	μΑ

*Note1: This specification is guaranteed by design, not mass production tested.

*Note2: Vcelln means Cell-n's voltage. n=1, 2, 3

RECOMMENDED OPERATING CONDITIONS (ELECTRICAL CHARACTERISTICS)

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if when they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

OPERATION

VDET1n / Over-Charge Detectors (n=1, 2, 3)

While the cells are charged, the voltage between V_{C1} pin and V_{C2} pin (voltage of the Cell-1), the voltage between V_{C2} pin and V_{C3} pin (voltage of the Cell-2), and the voltage between V_{C3} pin and V_{SS} pin (voltage of the Cell-3) are supervised. If at least one of the cells' voltage becomes equal or more than the over-charge detector threshold, the over-charge is detected, and an external charge control Nch MOSFET turns on with C_{OUT} pin being at "H" level and by cutting a fuse on the charger path, and charge stops.

To reset the over-charge and make the C_{OUT} pin level to "L" again after detecting over-charge, in such conditions that a time when all the cells' voltages are down to a level lower than over-charge released voltage.

Internal fixed output delay times for over-charge detection, over-charge detector timer reset, release from over-charge exist. Even if one of voltage of the cells keeps its level more than the over-charge detector threshold, and output delay time passes, over-charge voltage is detected. If all the cell voltages become lower than the over-charge detector threshold within the output delay time of over-chare detector by noise or other reasons, the time period is less than over-charge detector timer reset output delay time, the over-charge delay time is accumulated and maintained, and the accumulated delay time reaches the output delay time of over-charge, the over-charge is detected. After detecting over-charge, even if all the cell voltages become equal or less than the released voltage from over-charge, if at least one of the cells voltage becomes higher than the released voltage from over-charge within the output delay time of the release from over-charge, then over-charge is not released.

The output type of the Cout pin is CMOS output between Vss and the built-in regulator, and "H" level of Cout pin is the output voltage of the built-in regulator. (Typ. 4.7V)

Shutdown Function

The voltage between V_{C1} pin and V_{C2} pin (the voltage of Cell-1), the voltage between V_{C2} pin and V_{C3} pin (Cell-2 voltage), and the voltage between V_{C3} pin and V_{SS} pin (Cell-3 voltage) are supervised. If all the cells voltages become equal or less than the shutdown detector threshold, all the circuits are halted and shut down, as a result, the consumption current of IC itself (Shutdown current) is extremely reduced. (Max. 0.1μ A)

After detecting shutdown, at least one of the cell voltages becomes equal or more than the shutdown detector threshold, the shutdown state is released.

• DS (Delay Shortening) Function

By connect short 2 cells other than monitored cell, over-charge and released delay time can be shortened. Table of the cell of delay time shortened and direct wiring positions

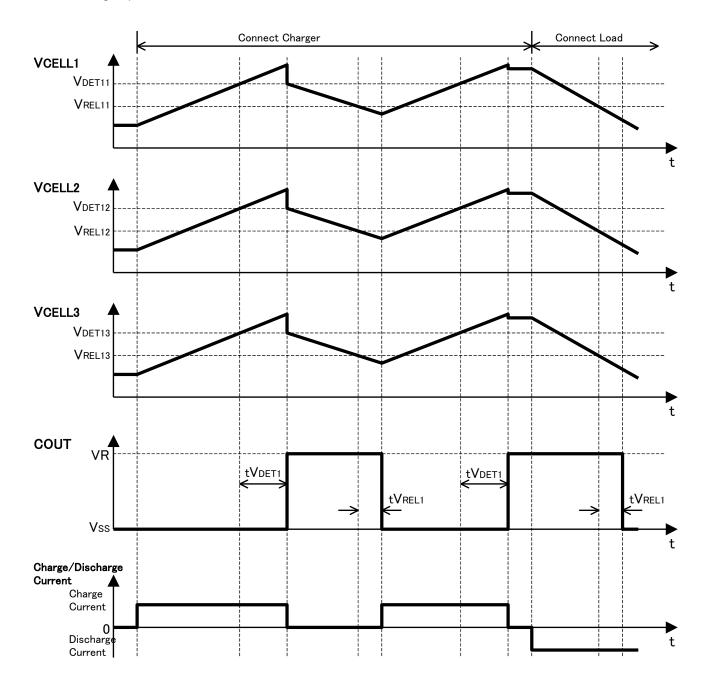
Delay time shortened CELL	Direct wiring positions
CELL1	V_{C2} pin and V_{C3} pin, V_{C3} pin and V_{SS} pin
CELL2	V _{C1} pin and V _{C2} pin, V _{C3} pin and V _{SS} pin
CELL3	V_{C1} pin and V_{C2} pin, V_{C2} pin and V_{C3} pin

• 2-cell/ 3-cell protection alternative

When the IC should be used as a 2-cell protection IC, connect short Vc3 pin and Vss pin.

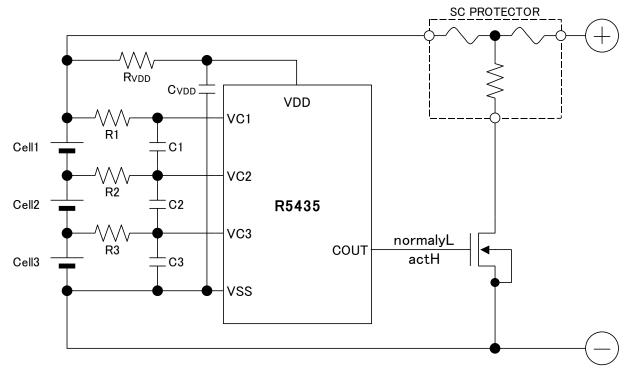
TIMING CHART

Over-charge operation

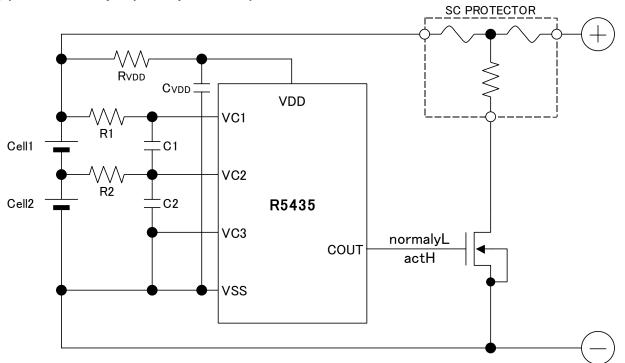


TYPICAL APPLICATIONS

(1) Circuit example (3-cell protection)



(2) Circuit example (2-cell protection)



*In terms of the order of connecting cells, the positive terminal of the cell 1 should be the last. Otherwise, COUT may output "H" tentatively, and the fuse may be fused.

External parts ratings

Symbol	Тур.	Unit	Range	
Rvdd	100	Ω	100~1000	
R1	1000	Ω	330~1000	
R2	1000	Ω	330~1000	
R3	1000	Ω	330~1000	
CVDD	0.1	uF	0.01~1	
C1	0.1	uF	0.01~1	
C2	0.1	uF	0.01~1	
C3	0.1	uF	0.01~1	

Technical Notes

The voltage fluctuation is stabilized with R_{VDD} and C_{VDD}. If a small R_{VDD} is set, in the case of the large transient may happen to the cell voltage, by the flowing current, the IC may be unstable. If a large R_{VDD} is set, by the consumption current of the IC itself, the voltage difference between V_{DD} pin and V_{C1} pin is generated, and unexpected operation may result. Therefore, the appropriate value range of R_{VDD} is from 100Ω to $1k\Omega$. To make a stable operation of the IC, the appropriate value range of C_{VDD} is from 0.01μ F to 1.0μ F.

The voltage fluctuation is stabilized with R1 to R3 and C1 to C3. If a R1 to R3 is too large, by the conduction current at detection, the detector threshold may shift higher. Therefore, the appropriate value range of R1 to R3 is equal or less than $1k\Omega$. To make a stable operation of the IC, the appropriate value range of C1 to C3 is $0.01\mu F$ or more.

The typical application circuit diagrams are just examples. This circuit performance largely depends on the PCB layout and external components. In the actual application, fully evaluation is necessary.

Over-voltage and the over current beyond the absolute maximum rating should not be forced to the protection IC and external components. During the time until the fuse is open after detecting over-charge, a large current may flow through the FET. Select an FET with large enough current capacity in order to endure the large current.

Ricoh cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Ricoh product. If technical notes are not complied with the circuit which is used Ricoh product, Ricoh is not responsible for any damages and any accidents.

To connect the SC protector, connect the SC protector to the cell must be the last.

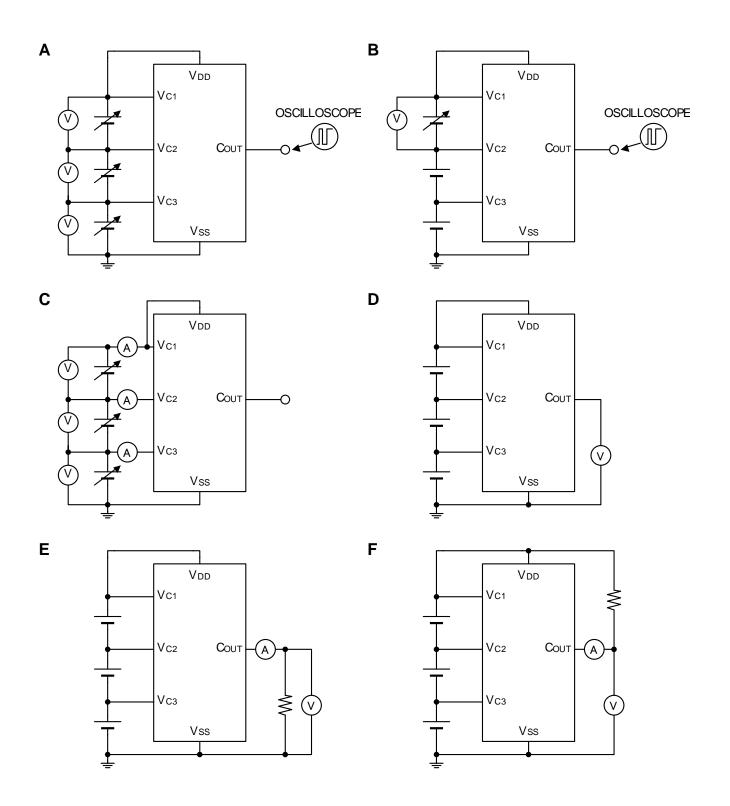
*SC protector

Contact: Sony Chemical & Information Device Company Ltd.

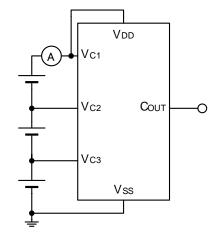
Zip code 141-0032

1-11-2 Osaki, Shinagawa, Tokyo Gate-city Osaki East Tower 8F Phone 03-5435-3946 http://www.sonycid.jp

TEST CIRCUITS



G



Typical Characteristics were obtained with using those above circuits:

Test Circuit A: Typical characteristics 1), 2)

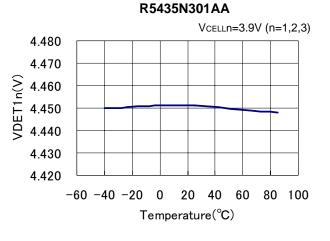
Test Circuit B: Typical characteristics 3), 4), 6)

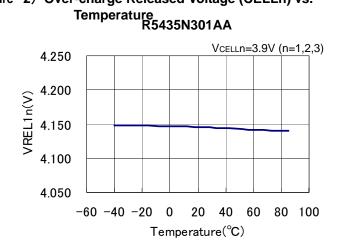
Test Circuit C: Typical characteristics 5)
Test Circuit D: Typical characteristics 7)
Test Circuit E: Typical characteristics 8)
Test Circuit F: Typical characteristics 9)
Test Circuit G: Typical characteristics 10), 11)

TYPICAL CHRACTERSTICS

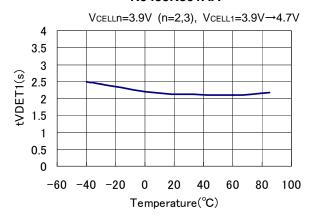
Part1. vs. Temperature

1) Over-charge voltage Threshold (CELLn) vs. Temperature 2) Over-charge Released Voltage (CELLn) vs.

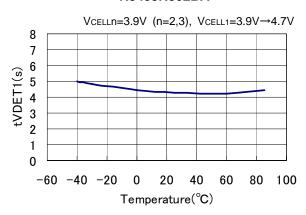




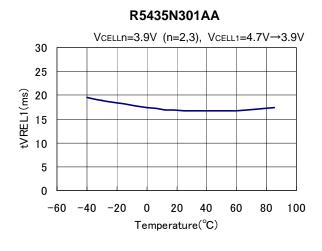
3) Output Delay of Over-charge vs. Temperature R5435N301AA



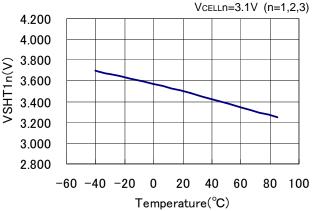
R5435N302BA



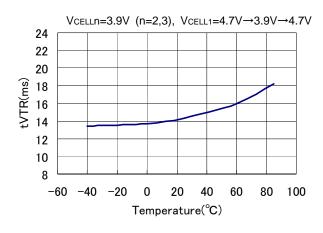
4) Output Delay of Release from Over-charge vs. Temperature 5) Shutdown Detector Threshold vs. Temperature

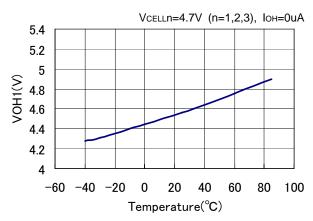


R5435N301AA

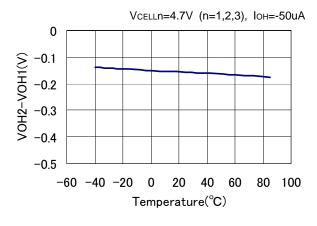


6) Output Delay of Over-charge Timer Reset vs. Temperature 7) Co∪⊤ Pch ON Voltage 1 vs. Temperature R5435N301AA R5435N301AA

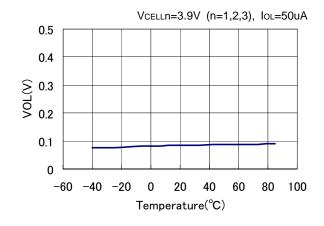




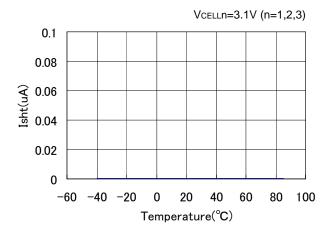
8) Cout Pch ON Voltage 2 vs. Temperature R5435N301AA



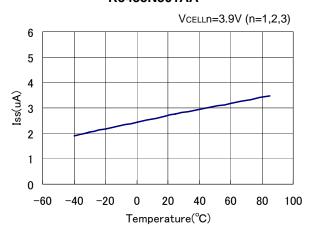
9) Cout Nch ON Voltage vs. Temperature R5435N301AA



10) Shutdown Current vs. Temperature R5435N301AA

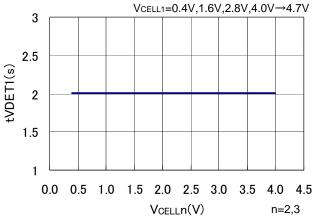


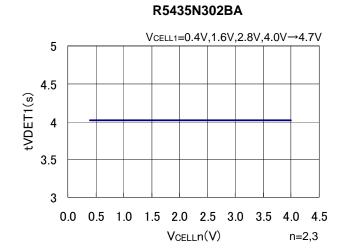
11) Supply Current vs. Temperature R5435N301AA



Part2. Delay Time dependence on VDD 1) Output Delay of Over-charge vs. V_{DD}

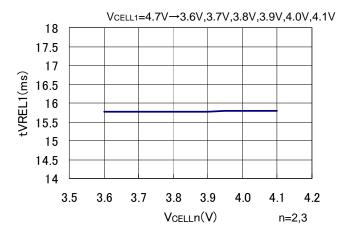
R5435N301AA 3





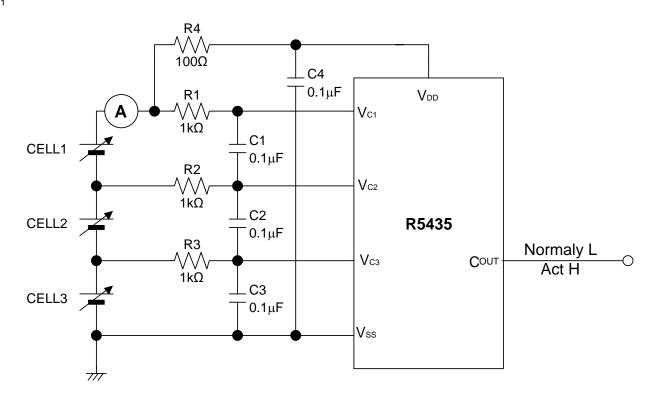
2) Output Delay of Release from Over-charge vs. V_{DD}

R5435N301AA

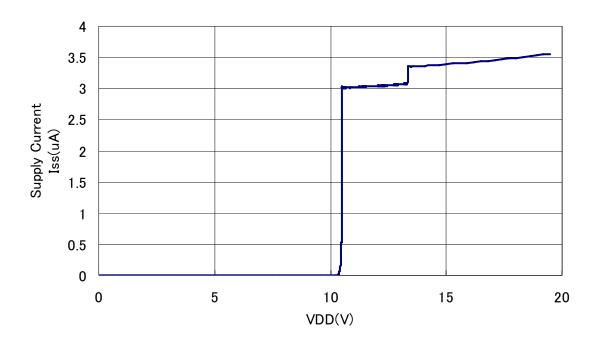


Part3. Supply Current dependence on V_{DD} (R5435N301AA)

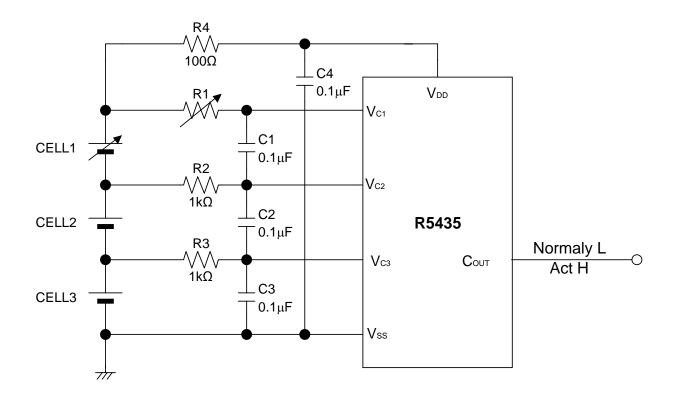
C1



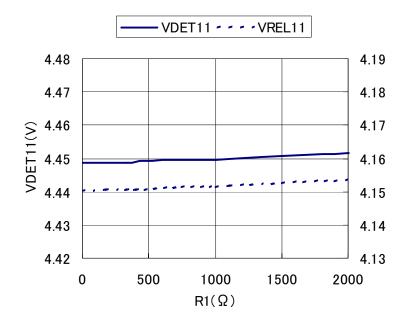
3-cell protector Supply Current vs. VDD



Part4. Over-charge detector, Release voltage from Over-charge dependence on External Resistance value (R5435N301AA)



Over-charge Detector/Released Voltage from Over-charge vs. R1 (CELL1)





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